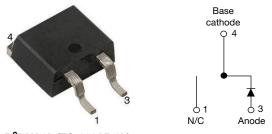
Vishay Semiconductors

## 650 V Gen 3 Power SiC Merged PIN Schottky Diode, 12 A



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D<sup>2</sup>PAK 2L (TO-263AB 2L)

### LINKS TO ADDITIONAL RESOURCES





PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub> 12 A								
V <sub>R</sub>	650 V							
V <sub>F</sub> at I <sub>F</sub> at 150 °C	1.50 V							
T <sub>J</sub> max.	175 °C							
I <sub>R</sub> at V <sub>R</sub> at 175 °C	5 µA							
Q <sub>C</sub> (V <sub>R</sub> = 400 V)	34 nC							
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

### FEATURES

Majority carrier diode using Schottky technology on SiC wide band gap material



- Improved V<sub>F</sub> and efficiency by thin wafer COMPLIANT technology
   HALOGEN
   Resitive V<sub>F</sub> temperature coefficient for easy
   FREE
- $\bullet$  Positive  $V_{\mathsf{F}}$  temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245  $^{\circ}\mathrm{C}$
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

### MECHANICAL DATA

**Case:** D<sup>2</sup>PAK 2L (TO-263AB 2L) Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise specified)							
PARAMETER SYMBO		TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V <sub>RRM</sub>		650	V			
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 125 °C (DC)	12	А			
DC blocking voltage	V <sub>DC</sub>		650	V			
Repetitive peak forward current	I <sub>FRM</sub>	$T_{C}$ = 25 °C, f = 50 Hz, square wave, DC = 25 %	48				
	I <sub>FSM</sub>	$T_{C} = 25 \text{ °C}, t_{p} = 10 \text{ ms}, \text{ half sine wave}$	83	А			
Non-repetitive peak forward surge current		$T_{C}$ = 110 °C, $t_{p}$ = 10 ms, half sine wave	74				
Power dissipation	P <sub>tot</sub> <sup>(1)</sup>	T <sub>C</sub> = 25 °C	72	v			
	Ptot ()	T <sub>C</sub> = 110 °C	32	~ ~ ~			
121	∫i <sup>2</sup> dt	T <sub>C</sub> = 25 °C	34.5	A 2 -			
l <sup>2</sup> t value		T <sub>C</sub> = 110 °C	27	A <sup>2</sup> s			
Operating junction and storage temperatures	T <sub>J</sub> <sup>(2)</sup> , T <sub>Stg</sub>		-55 to +175	°C			

#### Notes

<sup>(1)</sup> Based on maximum R<sub>th</sub>

 $^{(2)}$  The heat generated must be less than the thermal conductivity from junction-to-ambient: dP<sub>D</sub>/dT<sub>J</sub> < 1/R<sub> $\theta$ JA</sub>

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 Document Number: 97063

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# VS-3C12ET07S2L-M3

## **Vishay Semiconductors**

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS				MAX.	UNITS		
		I <sub>F</sub> = 12 A	-	1.3	1.5	v		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 12 A, T <sub>J</sub> = 150 °C	-	1.50	1.85			
		I <sub>F</sub> = 12 A, T <sub>J</sub> = 175 °C	-	1.58	-			
Reverse leakage current	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	0.8	65			
		$V_R = V_R$ rated, $T_J = 150 \ ^\circ C$	-	3	150			
		V <sub>R</sub> = V <sub>R</sub> rated, T <sub>J</sub> = 175 °C	-	5	-			
Total conceitance	С	V <sub>R</sub> = 1 V, f = 1 MHz	-	535	-	рF		
Total capacitance	U	V <sub>R</sub> = 400 V, f = 1 MHz	-	54	-	p		
Total capacitive charge	Q <sub>C</sub>	V <sub>R</sub> = 400 V, f = 1 MHz	-	34	-	nC		

<b>THERMAL - MECHANICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25 °C unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS								
Thermal resistance, junction to case	R <sub>thJC</sub>		-	1.6	2.1	°C/W		
Marking device	3C12ET07S							

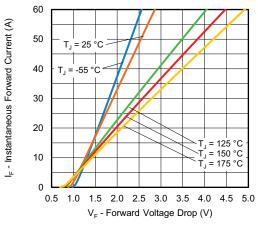


Fig. 1 - Typical Forward Voltage Drop Characteristics

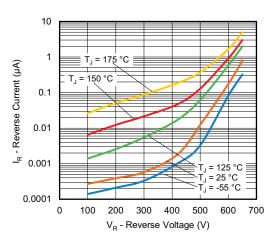


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

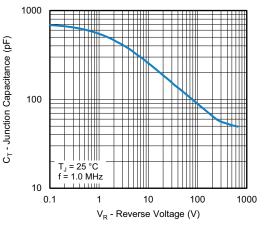


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

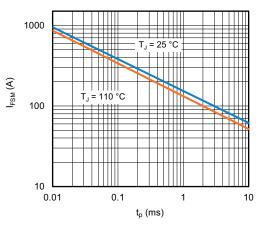


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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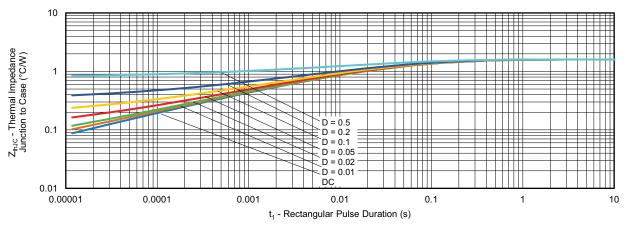
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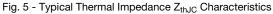
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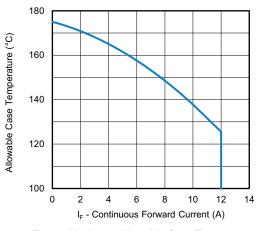


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

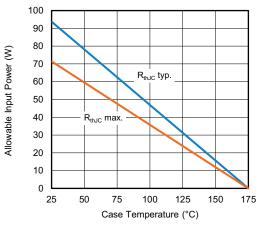


Fig. 7 - Forward Power Loss Characteristics

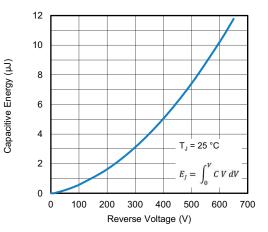


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

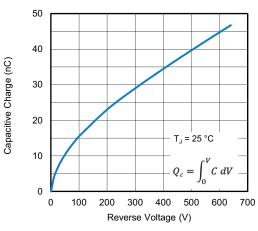


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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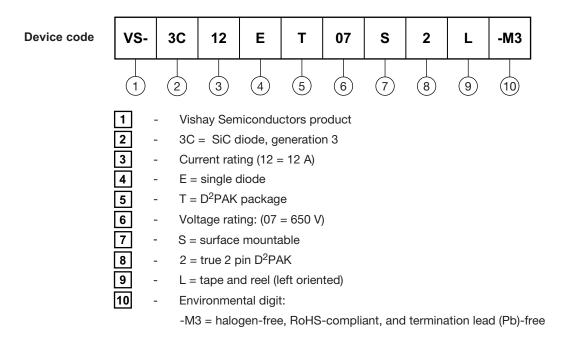
## VS-3C12ET07S2L-M3

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**ORDERING INFORMATION TABLE** 

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ORDERING INFORMATION						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-3C12ET07S2L-M3	800 per reel	13" diameter reel				

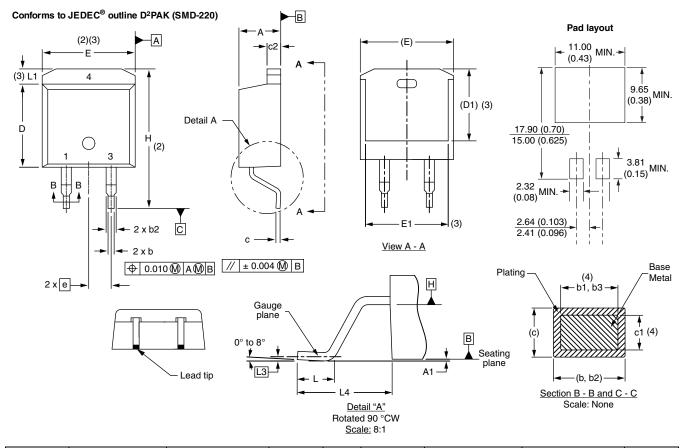
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96683				
Part marking information	www.vishay.com/doc?96693				
Packaging information	www.vishay.com/doc?95032				

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D<sup>2</sup>PAK 2L (TO-263AB 2L)

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	NOTES S	SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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